

| Ref # | Hits  | Search Query  | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|-------|---|---|------------------|---------|------------------|
| S22 6 | 21005 | implant\$6 and (si silicon) near15 temperature  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:44 |
| S22 7 | 11908 | implant\$6 same (mask\$5 or pattern\$5) and (si silicon) near15 temperature   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:52 |
| S23 1 | 2589  | implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate and (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:53 |
| S23 0 | 3651  | implant\$6 same (mask\$5 or pattern\$5) and (silicon or si) near5 substrate and (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:53 |
| S22 9 | 10441 | implant\$6 same (mask\$5 or pattern\$5) and (silicon or si) near5 substrate and (si silicon) near15 temperature   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:53 |
| S22 8 | 10807 | implant\$6 same (mask\$5 or pattern\$5) and (silicon or si) near10 substrate and (si silicon) near15 temperature  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:53 |
| S23 2 | 1505  | implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate and (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) and @py<"2002"   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:54 |
| S23 3 | 577   | implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) and @py<"2002"  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:55 |
| S23 5 | 3     | (germanium or ge or fluorine or f neutral) near10 implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) same anneal\$6 and @py<"2002" | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/27 11:58 |

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|----------|-----|---|---|----|----|------------------|
| S23<br>4 | 121 | implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) same anneal\$6 and @py<"2002"                                     | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:45 |
| S22<br>3 | 29  | (yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in. and implant\$5 and (silicon or si) near10 single near2 crystal\$7   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:45 |
| S21      | 6   | ion near4 implant\$4 same (fl or flourine or fluorine) same (silicon or si) and "117"/\$4.ccls.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:45 |
| L3       | 30  | (yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in. and implant\$5 and (silicon or si) near10 single near2 crystal\$7   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:45 |
| L1       | 7   | ion near4 implant\$4 same (fl or flourine or fluorine) same (silicon or si) and "117"/\$4.ccls.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:45 |
| S22<br>1 | 80  | (yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:46 |
| S20<br>9 | 39  | ion near3 (germanium or ge fluorine f) near3 implant\$5 near15 (si or silicon) near5 (substrate or wafer) near15 (mask\$4 or pattern\$4)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:46 |
| S18<br>6 | 101 | (silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge) same (photo\$1resist or resist or mask\$4) same (si or silicon) near4 deposit\$4 | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:46 |
| L7       | 121 | implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) same anneal\$6 and @py<"2002"                                     | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:46 |

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| L6  | 102  | (silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge) same (photo\$1resist or resist or mask\$4) same (si or silicon) near4 deposit\$4 | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:46 |
| L5  | 40   | ion near3 (germanium or ge fluorine f) near3 implant\$5 near15 (si or silicon) near5 (substrate or wafer) near15 (mask\$4 or pattern\$4)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:46 |
| L4  | 82   | (yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:46 |
| L2  | 121  | implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) same anneal\$6 and @py<"2002"                                     | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:46 |
| L8  | 82   | (yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:52 |
| L12 | 11   | implant\$5 near10 (carbon or germanium or fluoride) same epitax\$6 near5 (si or silicon) near15 temperature   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:53 |
| L11 | 112  | implant\$5 near10 (carbon or germanium or fluoride) and epitax\$6 near5 (si or silicon) near15 temperature  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:53 |
| L10 | 334  | implant\$5 near10 (si or carbon or germanium or fluoride) and epitax\$6 near5 (si or silicon) near15 temperature  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:53 |
| L9  | 1150 | implant\$5 and epitax\$6 near5 (si or silicon) near15 temperature   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/07/09 18:53 |